

## ENGR 305 – Lab #7

### NPN at DC

#### OBJECTIVES:

To study DC biasing of an NPN bipolar transistor by:

- Completing the DC analysis of two circuits: (1) an NPN transistor that is biased in the active region and (2) an NPN transistor that is biased in the saturation region.
- Implementing the circuits in an experimental setting, taking measurements, and comparing their performance with theoretical and simulated results.
- Qualitatively seeing the impact of transistor-to-transistor variations.

#### MATERIALS:

- Laboratory setup, including breadboard
- 1 NPN transistor (2N3904)
- Several wires and resistors of varying sizes

#### PART 1: NPN IN ACTIVE MODE

Consider the circuit shown.

Design the circuit such that  $I_C = 1\text{ mA}$ ,  $V_B = 0\text{ V}$ , and  $V_C = +5\text{ V}$ . Use supplies of  $V_+ = 15\text{ V}$ . Use  $\beta = 100$ .

#### Hand calculations

- Sketch the circuit in your lab book, clearly labeling the transistor's three terminals.
- What are  $I_B$  and  $I_E$ ? Based on these numbers, what is  $V_E$ ?
- You now have enough information to calculate  $R_E$  and  $R_C$ . Are the calculated values available in your kit? Can you achieve these values by combining several resistors? Comment.
- Derive the Thevenin equivalent circuit of  $R_1$  and  $R_2$ . What values of  $R_1$  and  $R_2$  do you need to use to achieve  $V_B = 0$ ? Is the problem completely specified? If not, what needs to be specified?

#### Prototyping and Measurement

- Assemble the circuit onto a breadboard.
- Using a digital multimeter, measure  $V_E$ ,  $V_C$ , and  $V_B$ .
- Using a digital multimeter, measure all resistors to three significant figures.

### Post-Measurement Exercise

- What are the measured values of  $V_{BE}$  and  $V_{CE}$ ? How do they compare to your pre-lab calculations? Explain any discrepancies.
- Based on the measured values of  $V_C$  and  $V_E$  and your measured resistor values, what are the measured values of  $I_E$ ,  $I_C$  and  $I_B$  based on your lab measurements?

## PART 2: NPN IN SATURATION MODE

Redesign the circuit such that  $I_C = 1\text{ mA}$ ,  $I_E = 1.2\text{ mA}$ ,  $V_C = +2\text{ V}$ , and  $V_{CE} = 0.2\text{ V}$ . Use supplies of  $V_+ = -V_- = 15\text{ V}$ . Note that you must use the saturation model.

### Hand calculations

- Sketch the circuit in your lab book, clearly labeling the transistor's three terminals.
- Based on the specifications, calculate  $V_E$  and  $V_B$ .
- You now have enough information to calculate  $R_C$  and  $R_E$ . Are the calculated values available in your kit? Can you achieve this value by combining several resistors? Comment.
- What is  $\beta_{forced}$ ?
- What values of  $R_1$  and  $R_2$  do you need to use? Is the problem completely specified?

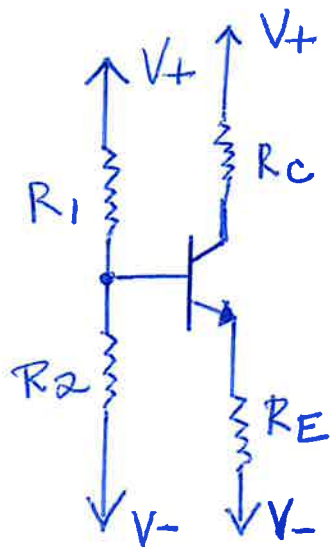
### Prototyping and Measurement

- Assemble the circuit onto a breadboard.
- Using a digital multimeter, measure  $V_E$ ,  $V_C$ , and  $V_B$ . Report them in your lab book.
- Using a digital multimeter, measure all resistors to three significant digits.

### Post-Measurement Exercise

- What are the measured values of  $V_{BE}$  and  $V_{CE}$ ? How do they compare to your pre-lab calculations? Explain any discrepancies.
- Based on the measured voltages and resistor values, what are the measured values of  $I_E$ ,  $I_C$  and  $I_B$  based on your lab measurements? What is  $\beta_{forced}$ ?

Part I and II (circuit)



Part 3: Diode-Connected NPN

